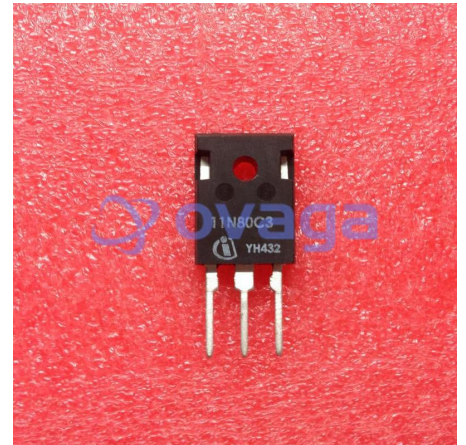


N-Channel MOSFETs (>500V...900V); Package: PG-TO247-3; VDS (max): 800.0 V;
 Package: TO-247; RDS(ON) @ TJ=25°C VGS=10: 450.0 mOhm; ID(max) @ TC=25°C:
 11.0 A; IDpuls (max): 33.0 A; MOSFET COOL MOS N-CH 800V 11A

| | |
|---------------|---|
| Manufacturers | Infineon Technologies Corporation |
| Package/Case | TO-247 |
| Product Type | Transistors |
| RoHS | |
| Lifecycle | |



Images are for reference only

Please submit RFQ for SPW11N80C3 or [Email to us: sales@ovaga.com](mailto:sales@ovaga.com) We will contact you in 12 hours.

[RFQ](#)

General Description

SPW11N80C3 is a power MOSFET transistor produced by Infineon Technologies. Here are some of its features:

Features

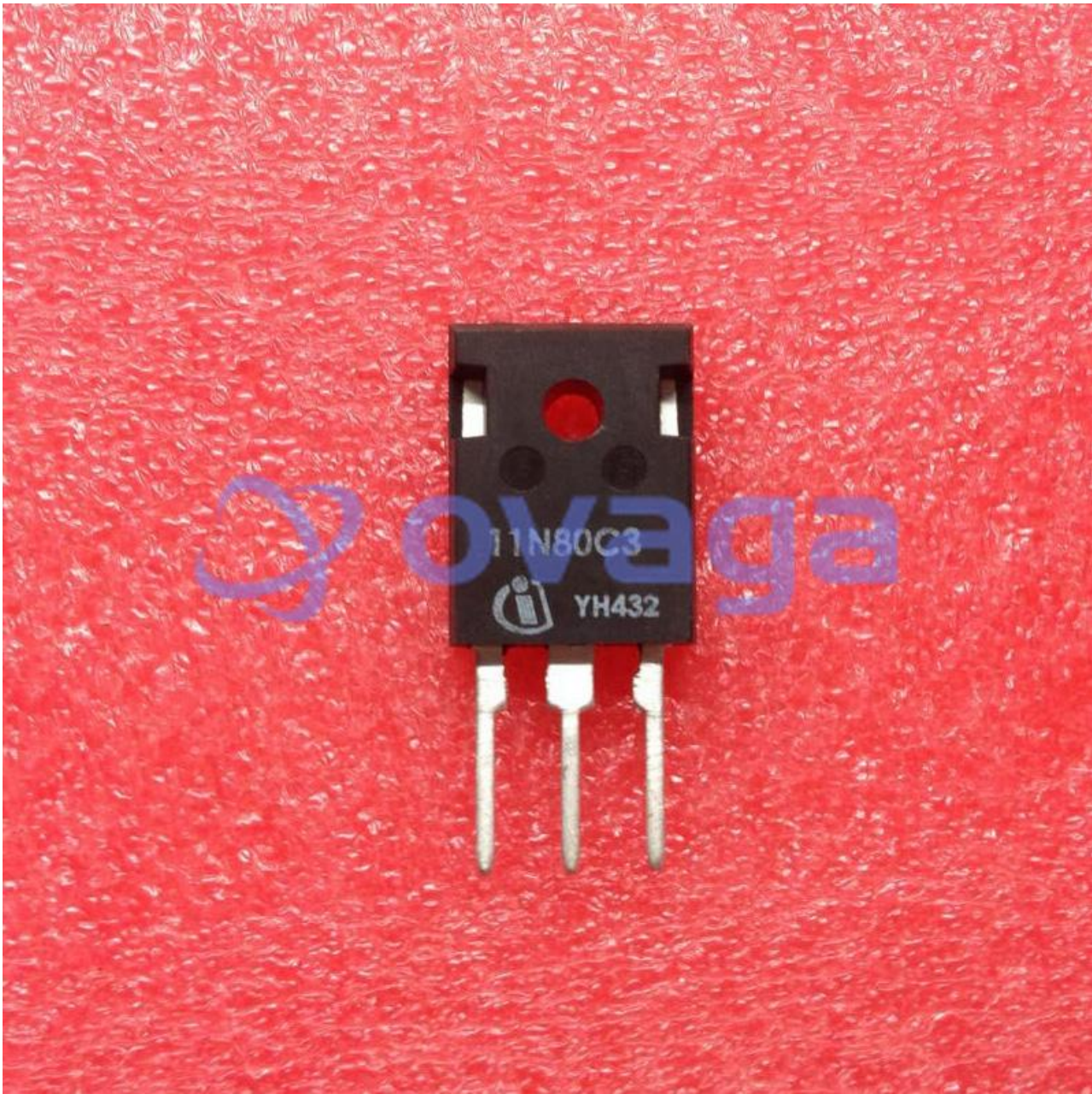
Drain-Source Voltage (V_{dss}): 800V

Continuous Drain Current (I_d): 11A

Power Dissipation (P_d): 130W

Gate Threshold Voltage (V_{gs}): between 2.5V and 4.5V

On-Resistance (R_{ds(on)}): 0.54Ω



Related Products



[BSP613P](#)

Infineon Technologies Corporation
SOT-223



[SPP11N65C3](#)

Infineon Technologies Corporation
TO-220



[SPP07N65C3](#)

Infineon Technologies Corporation
TO-220AB



[SPP07N60S5](#)

Infineon Technologies Corporation
P-TO220-3-1



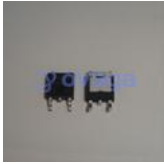
[SPP11N60C3XKSA1](#)

Infineon Technologies Corporation
PG-TO220



[IRF640NSPBF](#)

Infineon Technologies Corporation
PAK-3



[SPD03N60S5](#)

Infineon Technologies Corporation
TO-252



[SPP20N60CFD](#)

Infineon Technologies Corporation
TO-220AB